

Voids II+

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Void Nucleation Theory: Graphical depiction

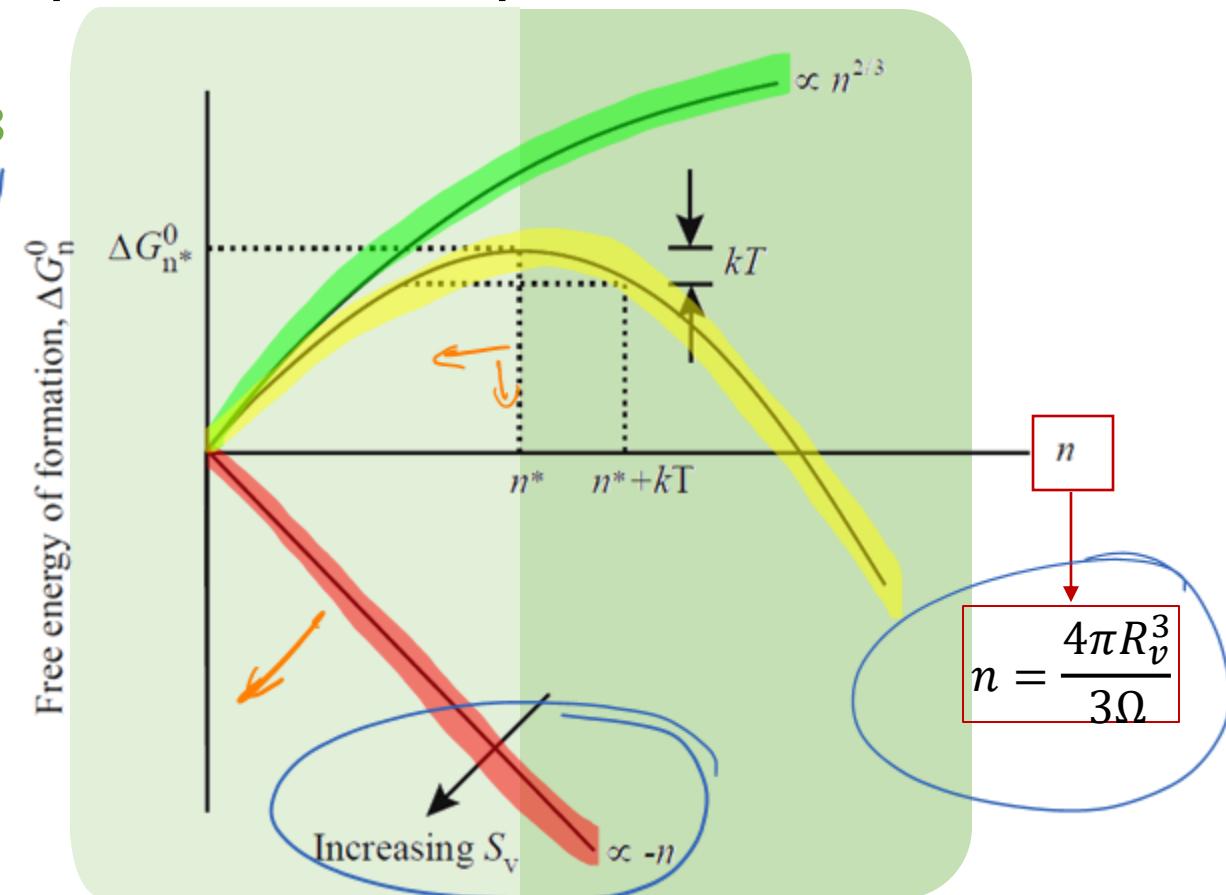
$$\Delta G_n^0 = -nkT \cdot \ln(S_v) + (36\pi\Omega^2)^{1/3} \gamma n^{2/3}$$

entropy of mixing of (negative)
 ↓ as decrease

interaction of interfacial surface $\propto 4\pi r^2 f$

$S_v \propto 1/n_{\text{nucl.}}$

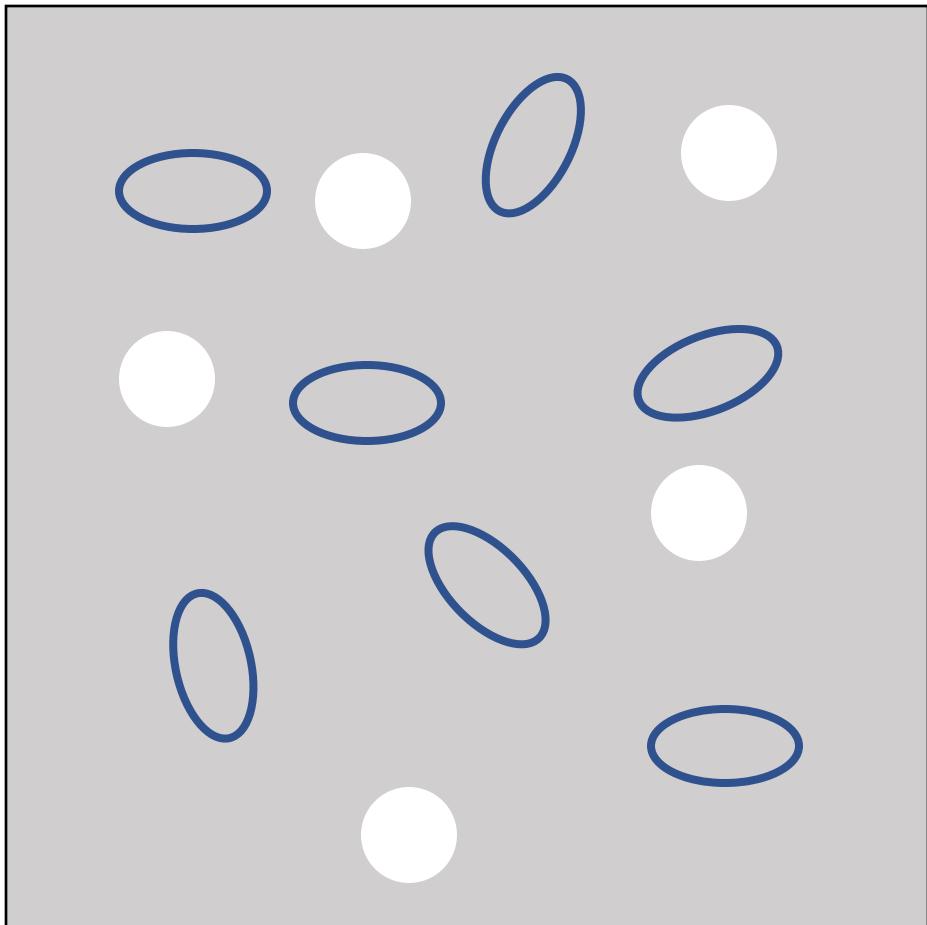
↑ Temp



Full derivations and discussion in Was 8.1

Fig. 8.2 Schematic illustration of ΔG_n^0 , the free energy of formation of a spherical void consisting of n vacancies and the effect of thermal fluctuations on the critical size void embryo

Void Growth – Simple Model



Let's assume a material with nucleated voids and dislocation loops only, then the total sink strength can be defined as (from Table 5.2 Was):

$$k_v^2 = z_v \rho_d + 4\pi R \rho_v$$

$$k_i^2 = z_i \rho_d + 4\pi R \rho_v$$

Void Growth

- For void growth, we need to know the net flux of vacancies to a void embryo. The net rate is thus a combination of the fluxes of interstitials and vacancies to a *nucleated* void, where:

$$J_{net}^V = J_v^V - J_i^V = 4\pi R\Omega D_v(C_v - C_v^V) - 4\pi R\Omega D_i(C_i - C_i^V)$$

$$J_{net}^V = dV/dt = 4\pi R\Omega(D_v C_v - D_i C_i)$$

$$dR/dt = \dot{R} = \frac{\Omega}{R} (D_v C_v - D_i C_i)$$

$$C_v^V = C_v^0 \exp\left(\frac{2\gamma\Omega}{Rk_b T}\right)$$

Void Growth

$$\frac{\partial C_v}{\partial t} = K_0 - K_{iv} C_i C_v - K_{vs} C_v C_s = 0$$

$$C_v = \frac{-K_{is} C_s}{2K_{iv}} + \left[\frac{K_0 K_{is}}{K_{iv} K_{vs}} + \frac{K_{is}^2 C_s^2}{4K_{iv}} \right]^{1/2}$$

Next slide

$$\frac{dR}{dt} = \dot{R} = \frac{\Omega}{R} (D_v C_v - D_i C_i)$$

$$C_i = \frac{-K_{vs} C_s}{2K_{iv}} + \left[\frac{K_0 K_{vs}}{K_{iv} K_{is}} + \frac{K_{vs}^2 C_s^2}{4K_{iv}} \right]^{1/2}$$

Next slide

$$\frac{\partial C_i}{\partial t} = K_0 - K_{iv} C_i C_v - K_{vs} C_i C_s = 0$$

Void Growth

Remember:

$$C_v = \frac{-K_{is}C_s}{2K_{iv}} + \left[\frac{K_0K_{is}}{K_{iv}K_{vs}} + \frac{K_{is}^2C_s^2}{4K_{iv}} \right]^{1/2}$$

and

$$C_i = \frac{-K_{vs}C_s}{2K_{iv}} + \left[\frac{K_0K_{vs}}{K_{iv}K_{is}} + \frac{K_{vs}^2C_s^2}{4K_{iv}} \right]^{1/2}$$

$$k_{jx}^2 = \frac{K_{jx}C_x}{D_j}$$

and

$$k_v^2 = z_v\rho_d + 4\pi R\rho_V$$

$$k_i^2 = z_i\rho_d + 4\pi R\rho_V$$

You can now pull all three equations above together to get:

$$C_v = \frac{D_v(4\pi R\rho_v + z_vp_d)}{2K_{iv}} (\sqrt{1+\eta} - 1)$$

$$C_i = \frac{D_i(4\pi R\rho_v + z_ip_d)}{2K_{iv}} (\sqrt{1+\eta} - 1)$$

Where:

$$\eta = \frac{4K_0K_{iv}}{D_iD_v(4\pi R\rho_v + z_vp_d)^2}$$

Void Growth

- With everything defined,

$$C_v = \frac{D_v(4\pi R\rho_v + z_vp_d)}{2K_{iv}}(\sqrt{1+\eta} - 1)$$

$$C_i = \frac{D_i(4\pi R\rho_v + z_ip_d)}{2K_{iv}}(\sqrt{1+\eta} - 1)$$

$$\eta = \frac{4K_0 K_{iv}}{D_i D_v (4\pi R\rho_v + z_vp_d)^2}$$

$$\frac{dR}{dt} = \dot{R} = \frac{\Omega}{R}(D_v(C_v - C_v^V) - D_i C_i)$$

- We can now rewrite the growth law as:

$$\dot{R}R = \frac{\Omega}{2K_{iv}} D_i D_v (z_i \rho_d - z_v \rho_d)(\sqrt{1+\eta} - 1)$$

Void Growth

$$R\dot{R} = K_o \Omega \left(\frac{z_i - z_v}{z_v} \right) \frac{z_v \rho_d}{(4\pi R \rho_v + z_v \rho_d)(4\pi R \rho_v + z_i \rho_d)} F(\eta)$$

- The **first term** is the main dpa-rate effect on void growth
- The **second term** is the “bias” term: if $Z_i = Z_v$, void growth is *impossible*
- The **third term** is the sink-strength balance term. Void growth is eliminated if there are too many or too few dislocations. Optimum growth occurs when the void sink term ($4\pi R \rho_v$) and the dislocation sink term ($z_v \rho_d$) are equal.
- The **fourth term** contains the effect of point defect recombination:

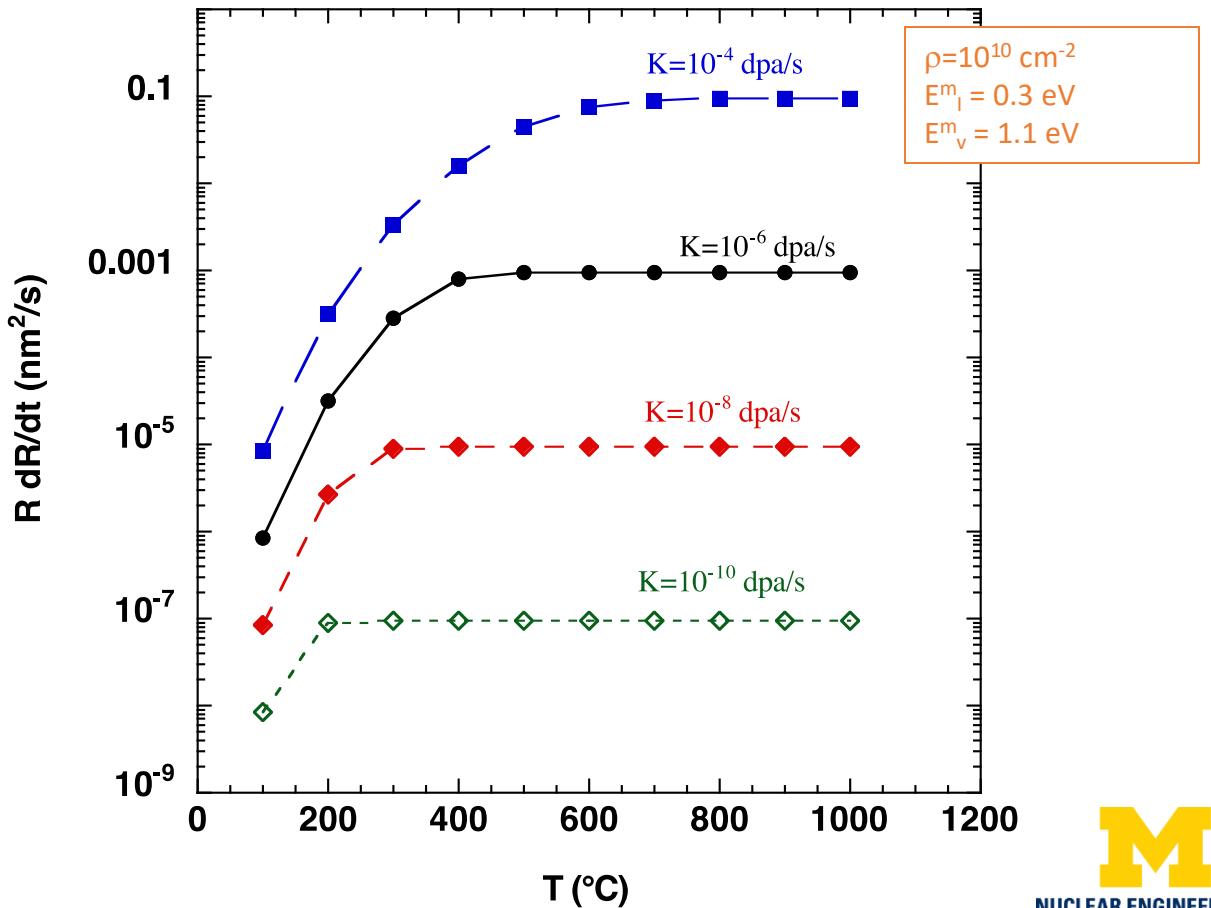
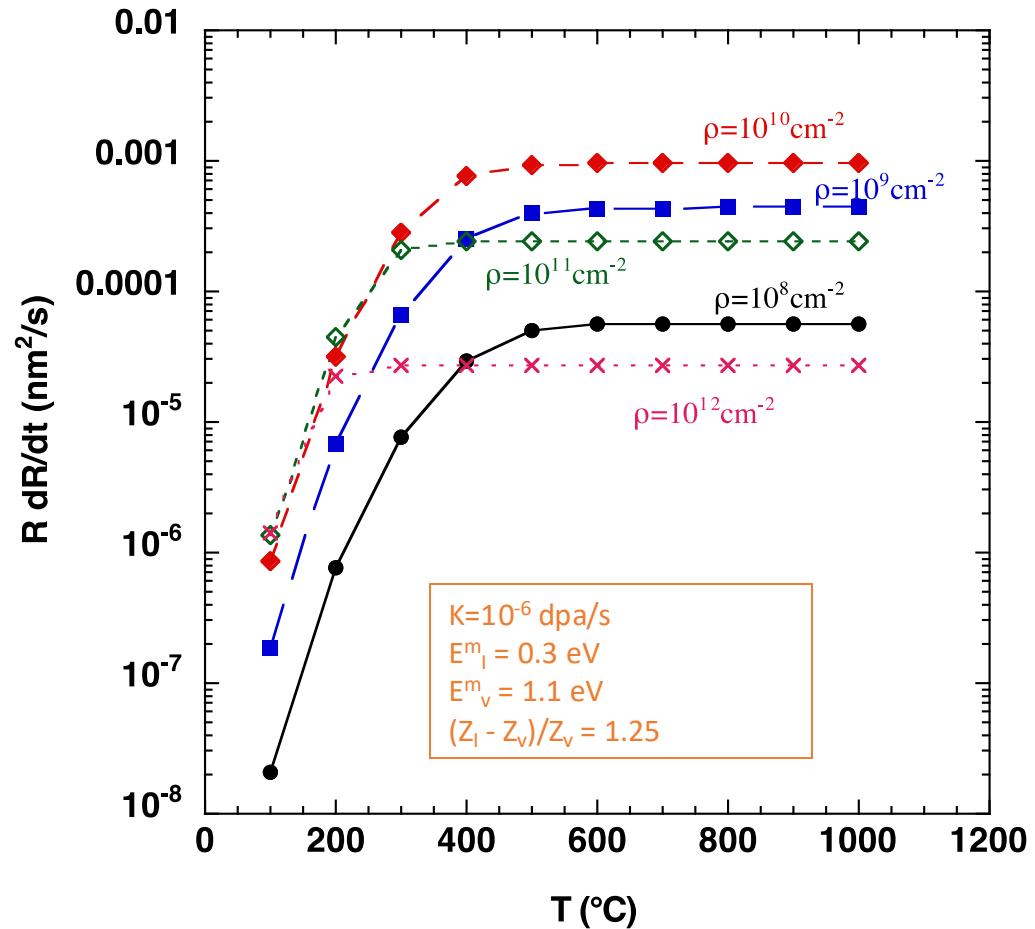
$$F(\eta) = 2(\sqrt{1+\eta} - 1)/\eta$$

Since η decreases with increasing temperature and F decreases with increasing η :

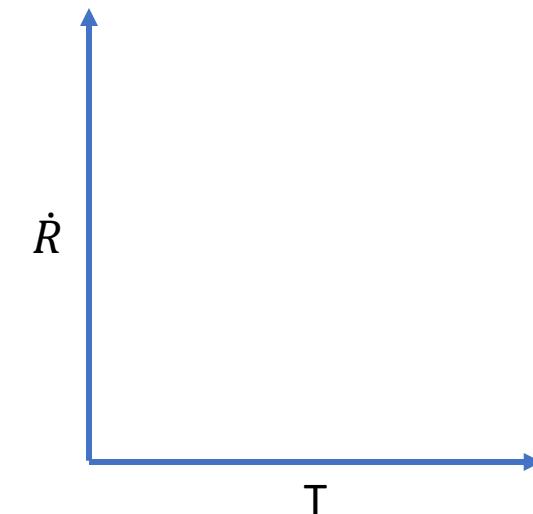
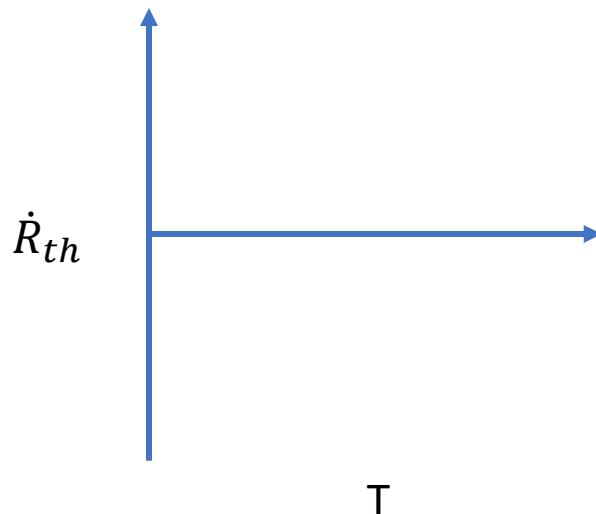
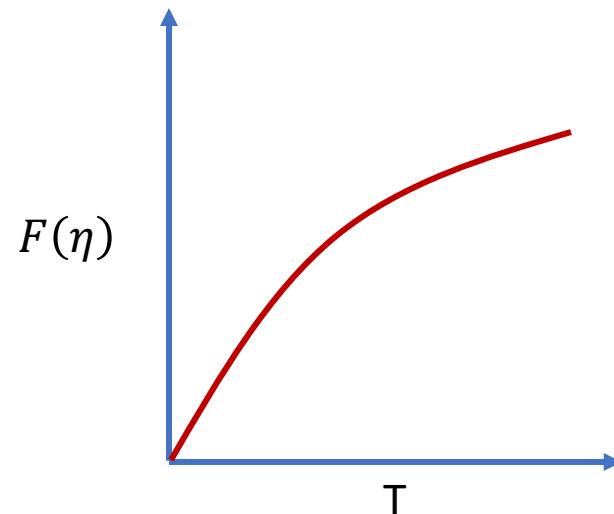
- At high temperature, $F \rightarrow 1$ and recombination does not effect void growth
- At low temperature, $F \rightarrow 0$ and recombination prevents void growth.

Void Growth

$$R \dot{R} = K_o \Omega \left(\frac{z_i - z_v}{z_v} \right) \frac{z_v \rho_d}{(4\pi R \rho_v + z_v \rho_d)(4\pi R \rho_v + z_i \rho_d)} F(\eta)$$



Void Swelling Temperature Dependence



At very high temperatures, void growth ceases because the vacancies “boil off” the voids. Repeating the previous derivation without neglecting C_v^0 gives the following shrinkage rate that competes with the growth rate:

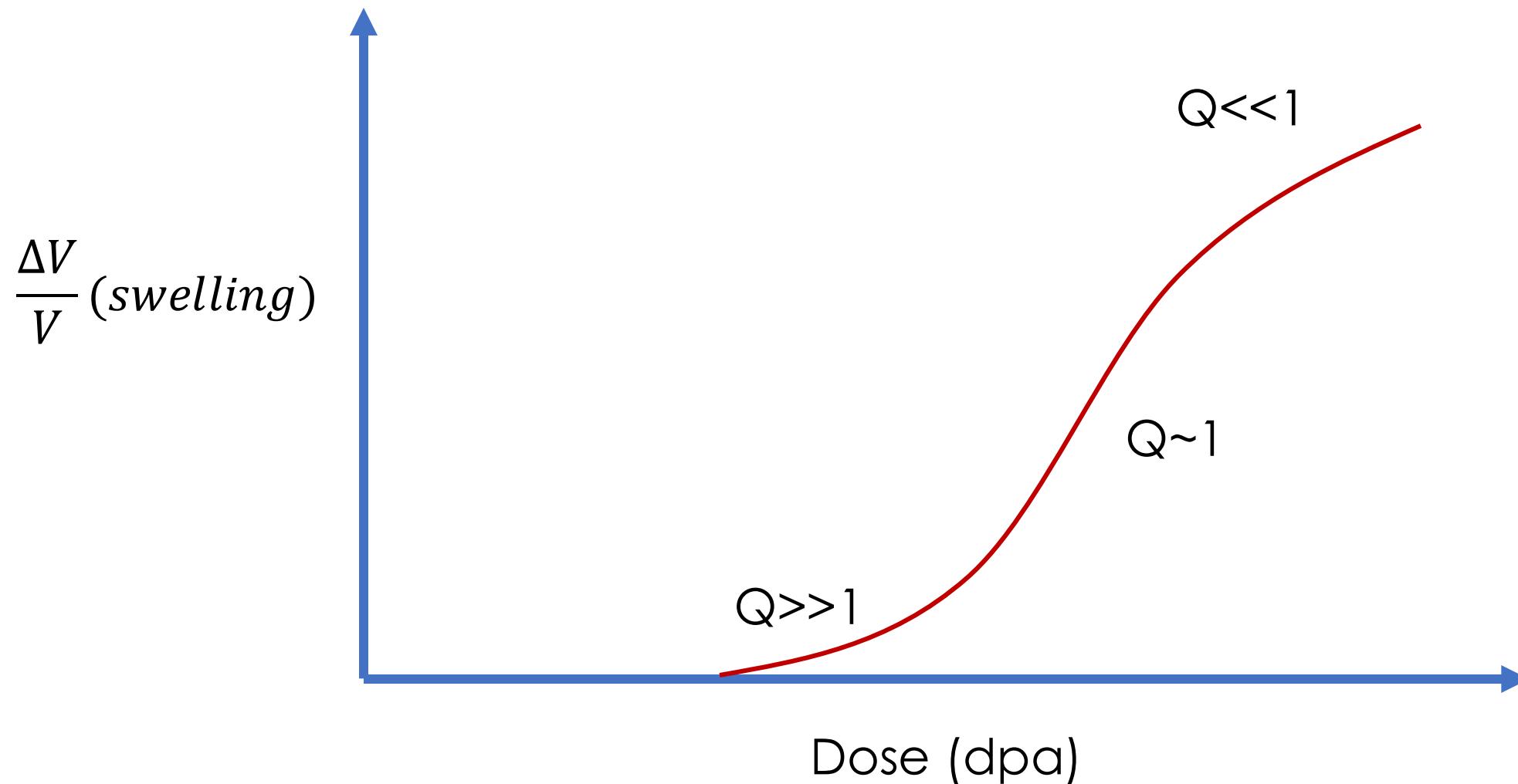
$$R\dot{R}_{th} = -\frac{D_v C_v^0 \Omega^2 z_v \rho_d}{kT(4\pi RN + z_v \rho_d)} (e^y - 1)$$

Effect of Structure on Void Swelling

- Ferritic steels swell at rates ~0.2%/dpa
- Structure alone is not sufficient to explain the difference between α -Fe (BCC) and γ -Fe (FCC)
- BCC vanadium alloys can swell at rates more like austenitic steels
- Difference is likely in the relative bias for point defects at sinks
- If the bias is removed: $z_i = z_v$, void growth is impossible
- Recall the 3rd term, put simply:

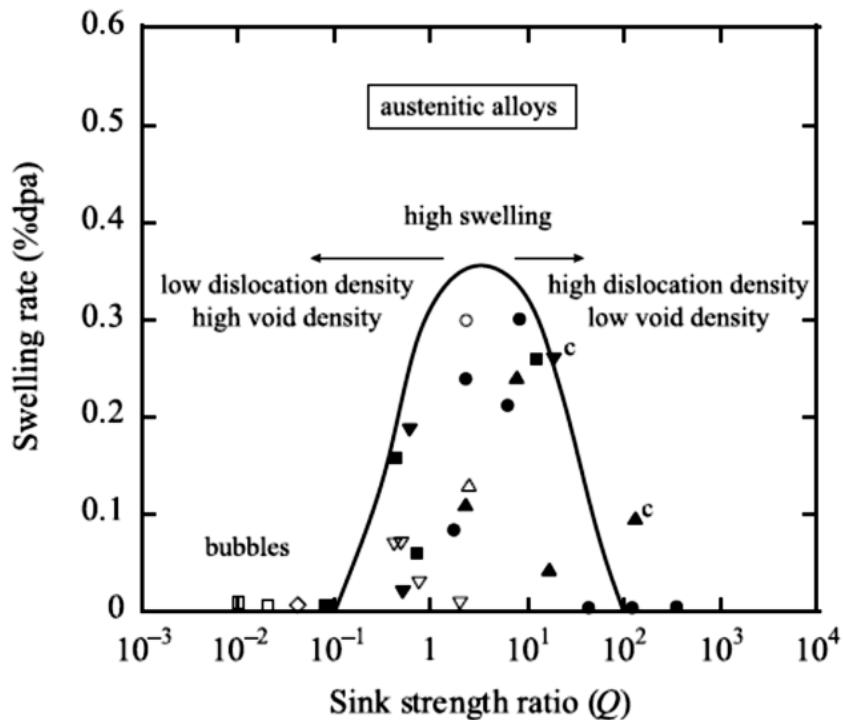
$$\left\{ \frac{z_v \rho_d}{(4\pi R \rho_v + z_v \rho_d)(4\pi R \rho_v + z_i \rho_d)} \right\} \frac{Q}{(1+Q)^2} \quad \text{Where: } Q = \frac{\rho_d z_i}{z_v 4\pi R \rho_v}$$

The Q-factor for structure dependence on dose



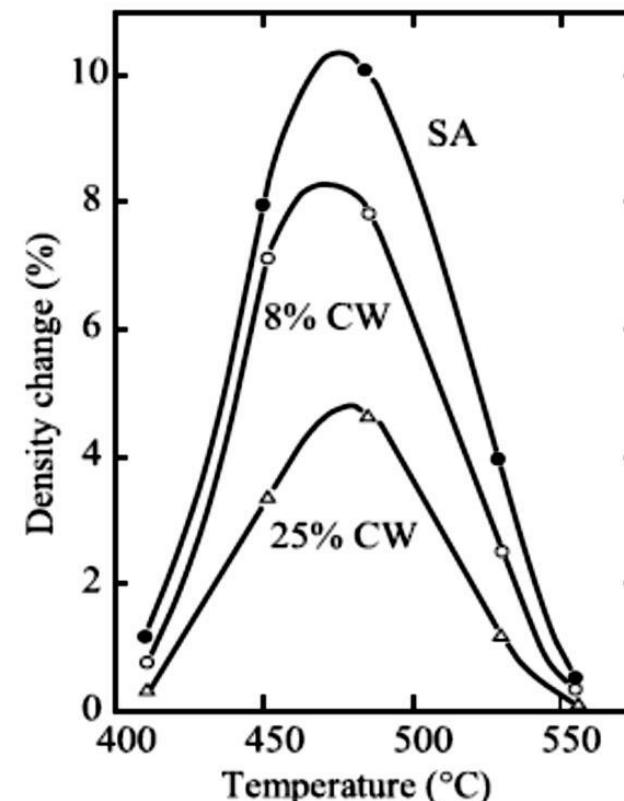
Effect of Structure on Void Swelling

● Johnston et al.
▲ Appleby et al.
■ Packan and Farrell
▼ Maziasz
▽ Sprague et al.
○ Westmoreland et al.
△ Smidt et al.
□ Tanaka et al.
◊ Lee and Mansur
c coalescence



Experimentally observed swelling rates as a function of Q for austenitic stainless steels (Mansur LK (1994) J Nucl Mater 216:97–123)

- Growth rate is maximum when $Q \sim 1$
- Growth decreases for $Q \neq 1$
- Observed experimentally
- CW reduces swelling because $Q \gg 1$



Dependence of swelling on cold-work for various temperatures for 316 stainless steel irradiated in the RAPSODIE reactor to doses of 20–71 dpa (Dupouy JM, Lehmann J, Boutard JL (1978) In: Proceedings of the Conference on Reactor Materials Science, vol. 5, Alushta, USSR. Moscow, USSR Government, pp 280–296)

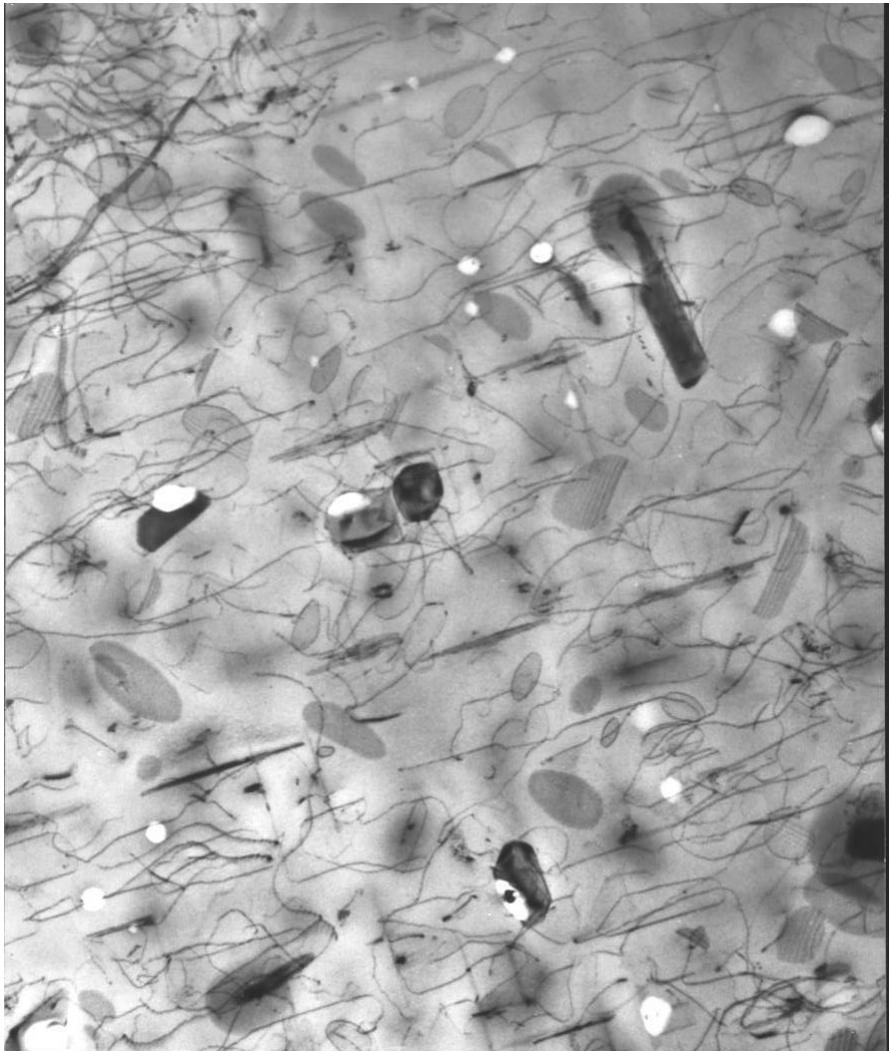


Based in Zeeland, Michigan, the iconic furniture company Herman Miller revolutionized office design forever when employee Robert Propst invented a modular, customizable system designed to give employees privacy and space. What year did Herman Miller introduce this invention, now famously known as the cubicle?

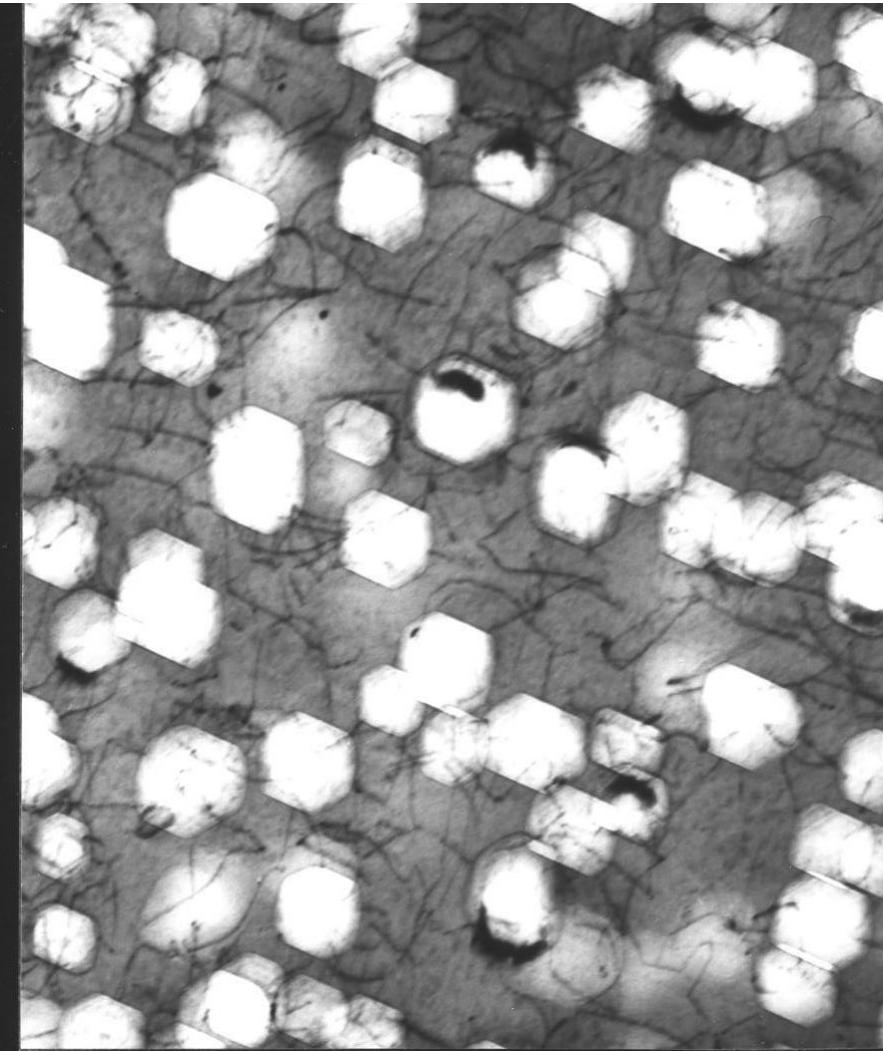


Image of voids + effect of sink strength

Commercial 316 SS (high sink strength)

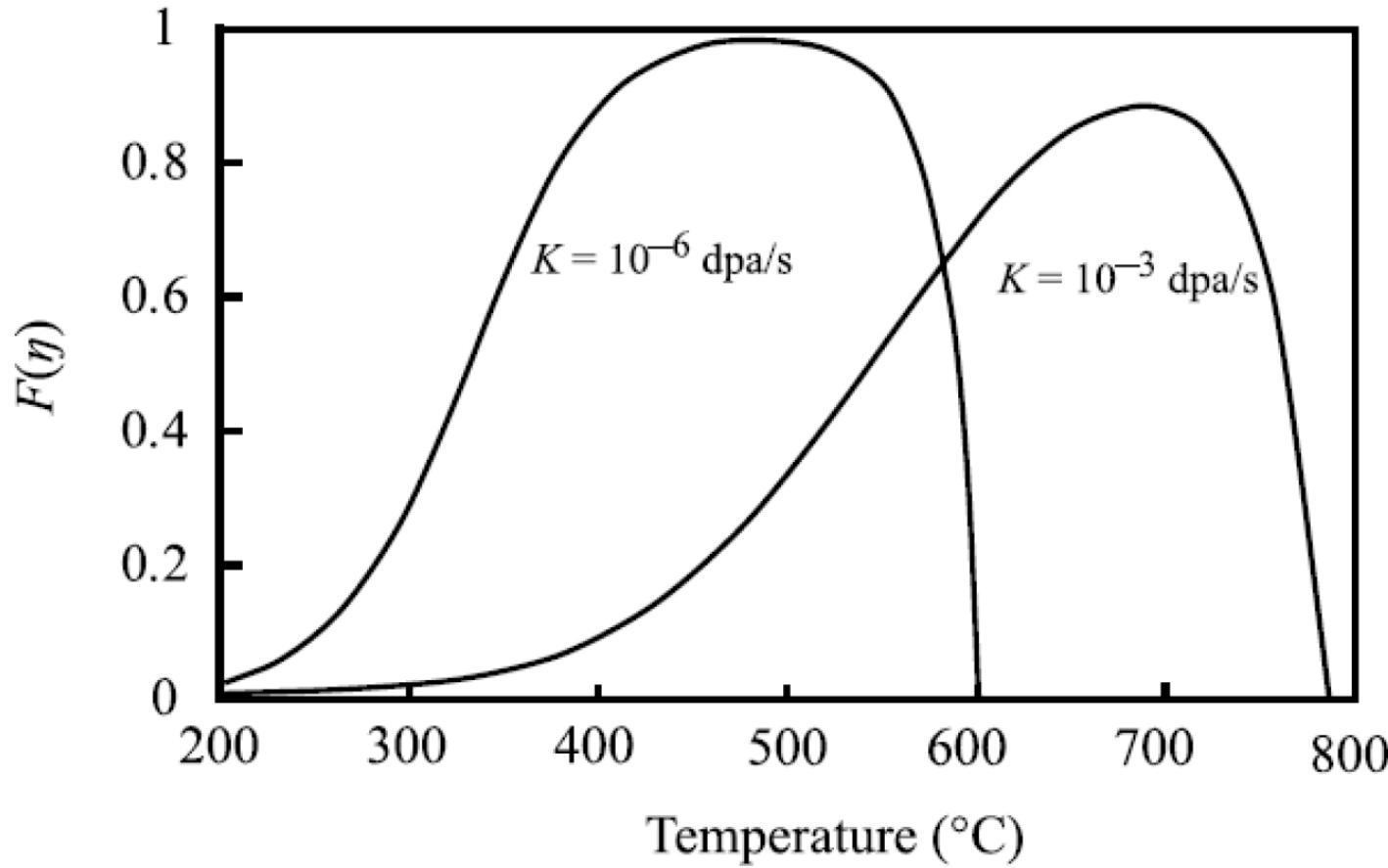


High-purity (low sink strength)



100 nm

Effect of Dose Rate



Dose rate is captured in the **fourth term** where:

$$F(\eta) = 2\left(\sqrt{1+\eta} - 1\right)/\eta$$

And:

$$\eta = \frac{4K_0 K_{iv}}{D_i D_v (4\pi R \rho_v + z_v p_d)^2}$$

Effect of Dose Rate

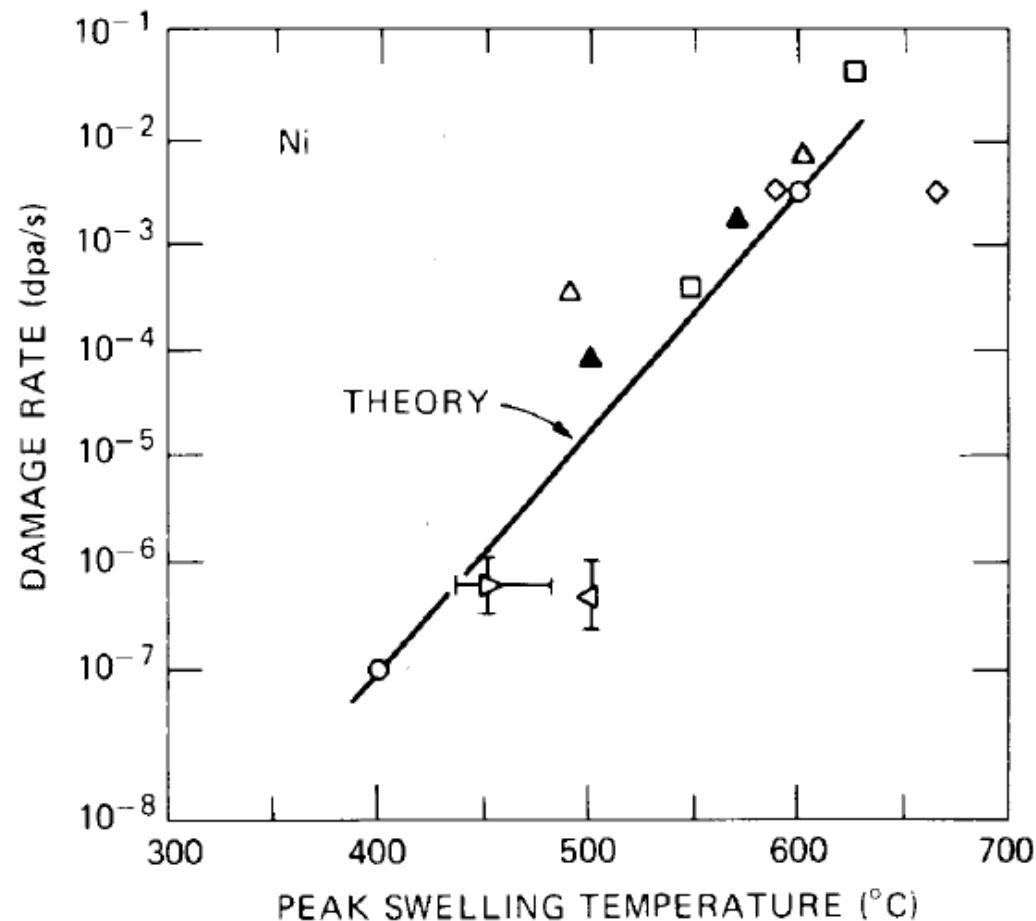


Figure 8.29. Compilation of experimental results for peak swelling temperature as a function of dose rate. Theoretically predicted trend is shown as the line. After Refs. 140 and 141.

Dose rate is captured in the **fourth term** where:

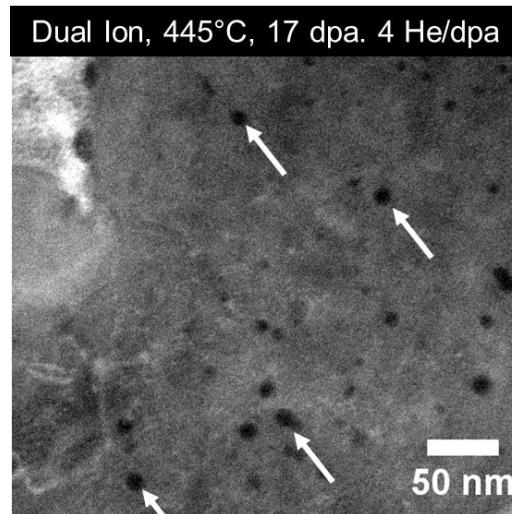
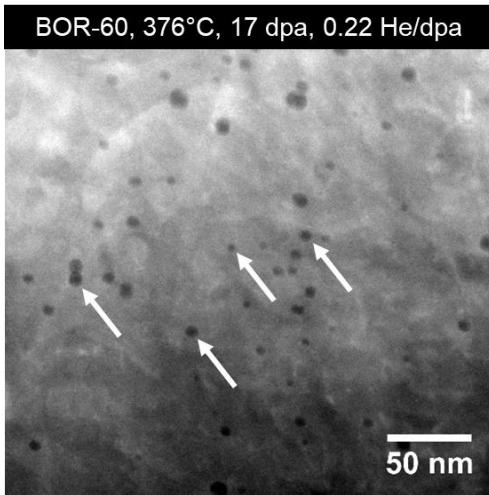
$$F(\eta) = 2\left(\sqrt{1+\eta} - 1\right)/\eta$$

And:

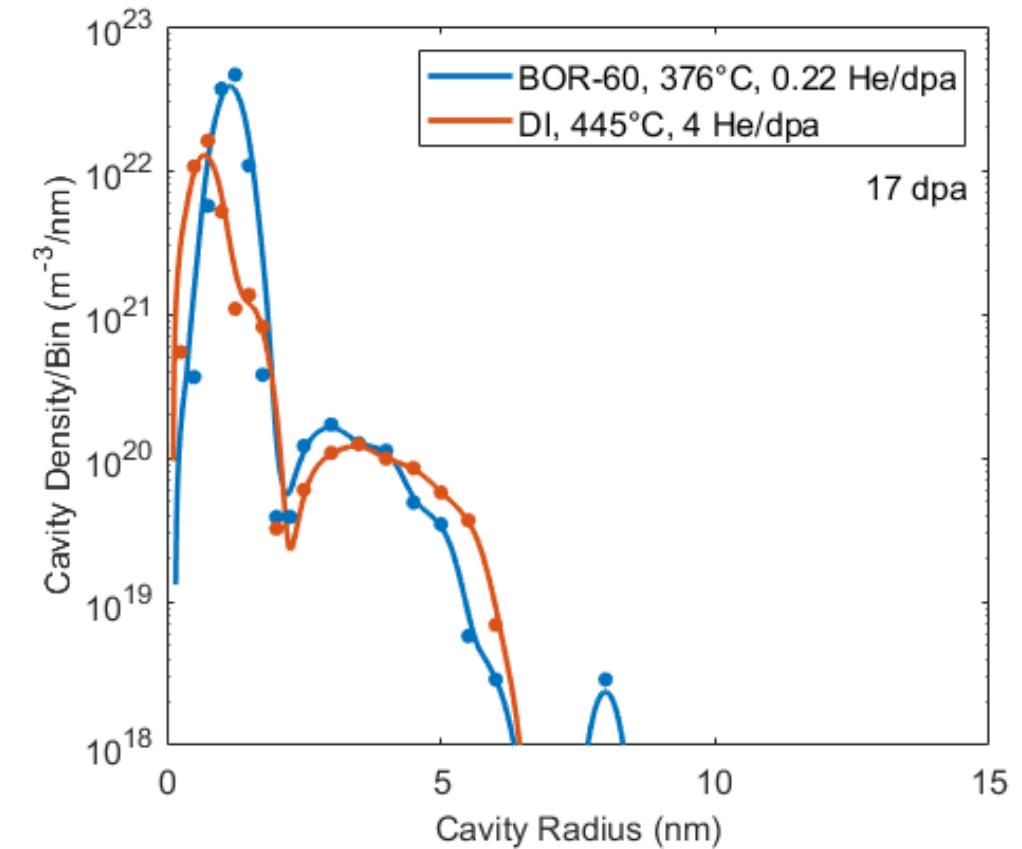
$$\eta = \frac{4K_0 K_{iv}}{D_i D_v (4\pi R \rho_v + z_v p_d)^2}$$

Effect of Dose Rate – Real World Example

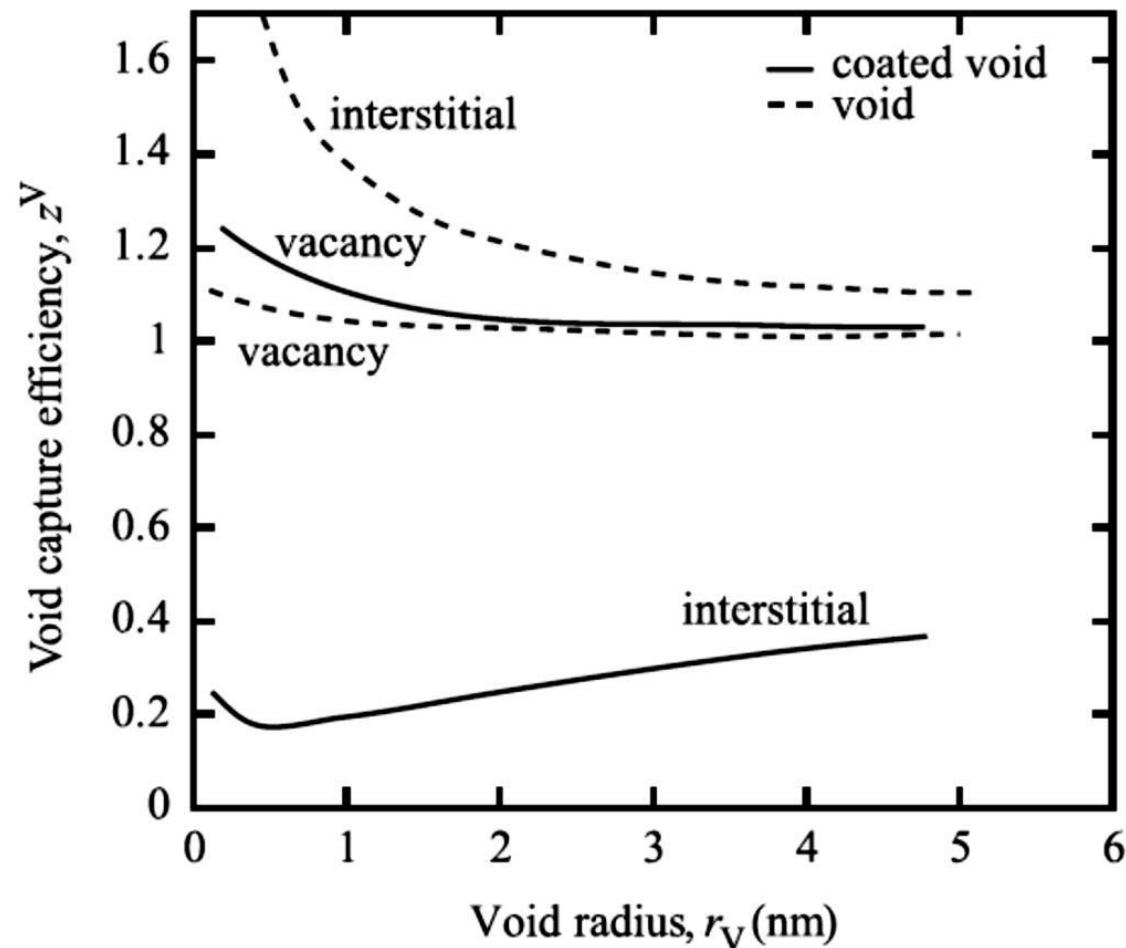
STEM HAADF



$$T_2 - T_1 = \frac{\frac{kT_1^2}{E_v^m + 2E_v^f} \ln \left(\frac{G_2}{G_1} \right)}{1 - \frac{kT_1}{E_v^m + 2E_v^f} \ln \left(\frac{G_2}{G_1} \right)}$$



Effect of void surface segregation on defect bias



- For a bare unpressurized void, **interstitial bias is greater than vacancy bias**. Voids will shrink
- If “shell” shear modulus or lattice parameter is greater than matrix shear modulus, **vacancy bias becomes greater than interstitial bias**
 - This effect can occur because of **radiation induced segregation**
- Thicker shells have a greater effect

Capture efficiency for point defects diffusion to a void and a coated void as a function of void radius RV . (W.G. Wolfer, L.K. Mansur, The capture efficiency of coated voids, Journal of Nuclear Materials, Volume 91, Issue 2, 1980, Pages 265-276)

Effect of Inert Gas: Bubbles & Voids

- Inert gas atoms (H, He, etc.) are created by transmutation and interact with vacancies
 - Must be accounted for on bubble/void growth as:
 - Insoluble gas atoms can act as immobile nucleation sites to which vacancies and interstitials migrate to form voids
 - Inert gas atoms can stabilize a cavity and assist the nuclei during nucleation and growth
- First, let's assume the following:
 - No account taken of cascades or lattice imperfections
 - Gas atom association is stable and mobile

Side Note!

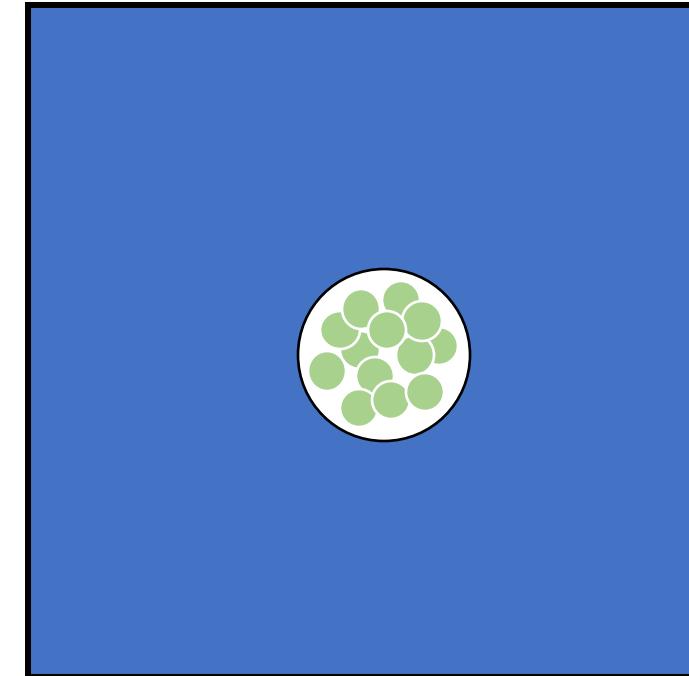
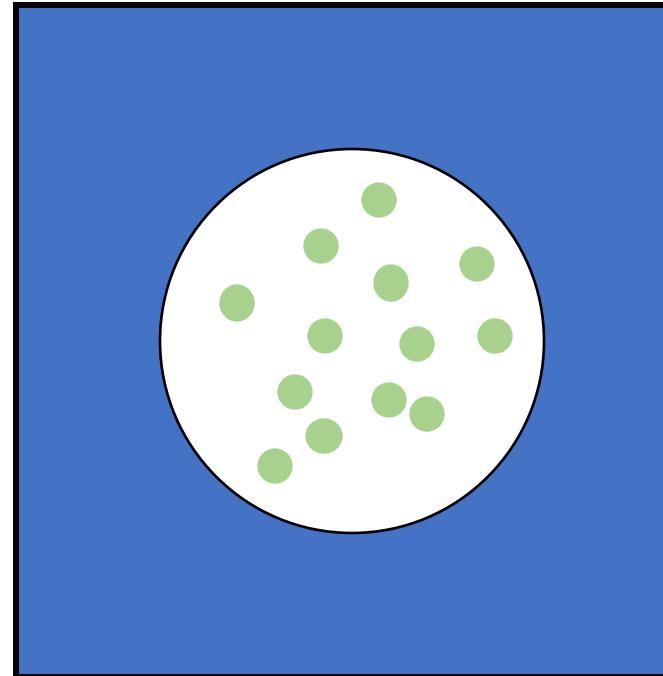
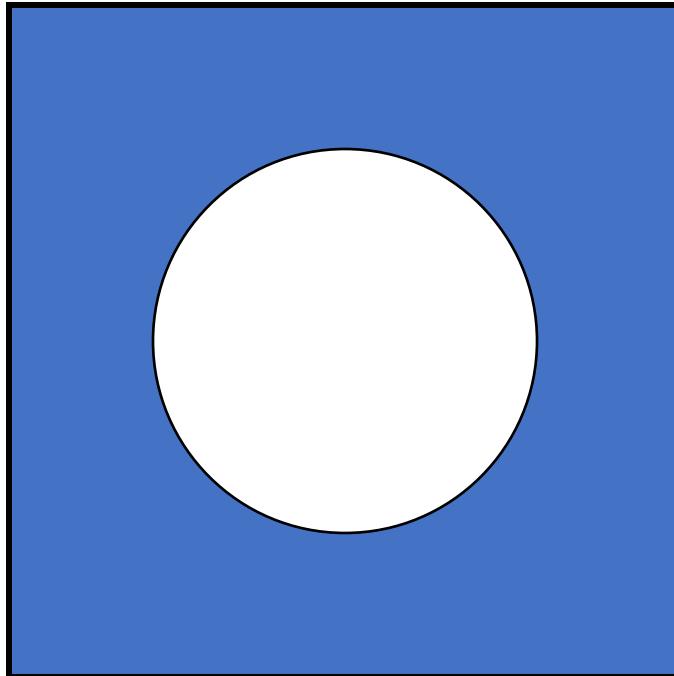
We generally define the following:

Void: open volume in a solid not pressurized by inert gas

Bubble: open volume in a solid that is pressurized by inert gas

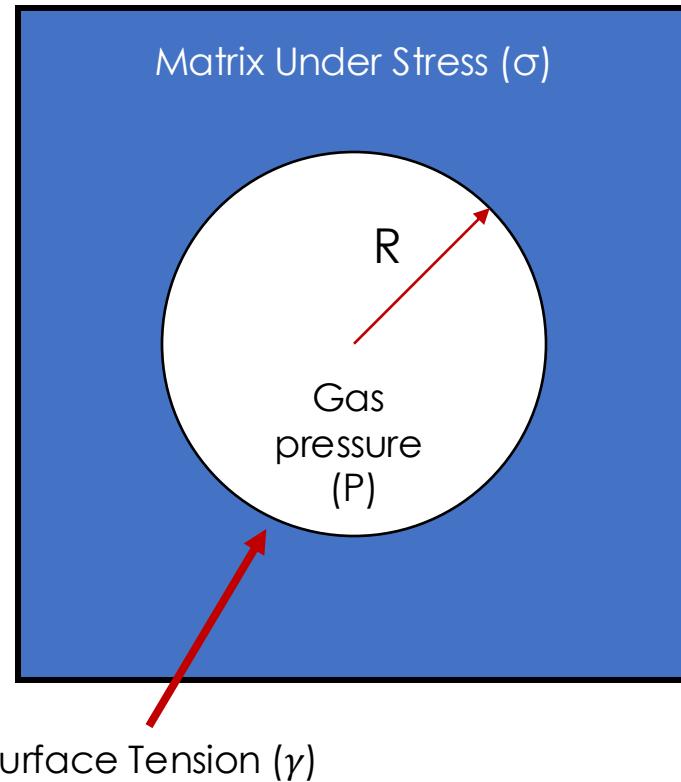
Cavity: Generalization for open volume in a solid – can be a bubble or void

Effect of Inert Gas: Bubbles & Voids

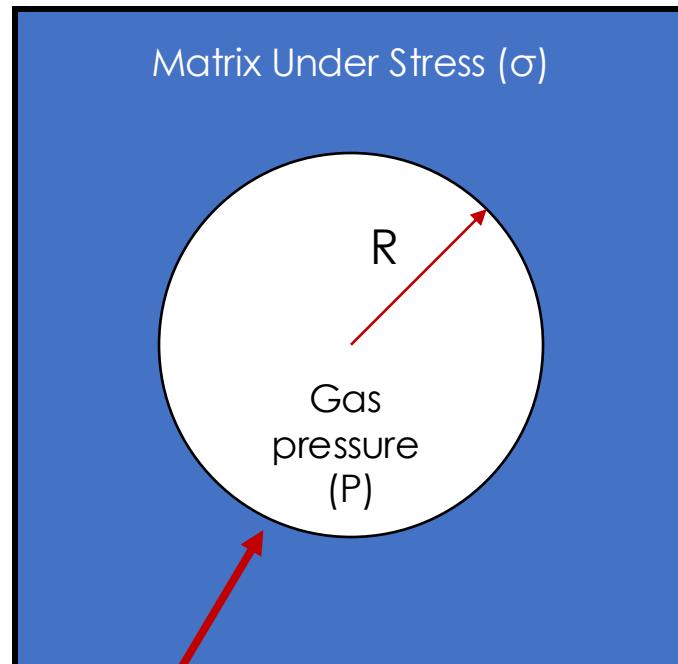


Effect of Inert Gas: Bubbles & Voids

- For a spherical cavity, the change in volume and surface area is:
- Under expansion (cavity growth) the pressure does work on $P dV$ and the surface energy increase by γdA , or simply,
- If not at mechanical equilibrium, then:



Effect of Inert Gas: Bubbles & Voids



- Let's now calculate the number of gas atoms present in the bubble, using the ideal gas law:
- Remembering that $P = \frac{2\gamma}{r}$ and plugging in we get:

Effect of Inert Gas: Bubbles & Voids

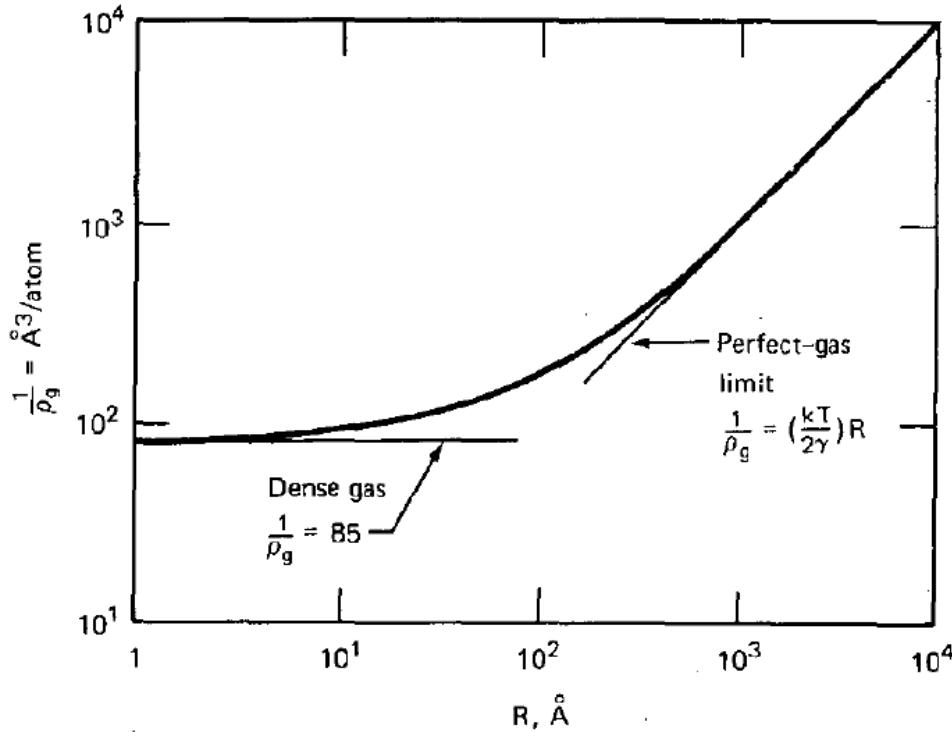


Fig. 13.3 Density of xenon gas in a spherical bubble imbedded in a stress-free solid of surface tension of 1000 dynes/cm.

For most applications we assume an ideal gas in mechanical equilibrium

- To account for non-ideal gas (e.g. high pressure in small bubbles) we need a different eq'n of state:
- We can then solve for n_x again using this relationship to get the number of gas atoms in the **dense gas limit**:

$$n_x = \frac{\frac{4}{3}\pi r^3}{B + \left(\frac{k_b T}{2\gamma}\right)r}$$

And for non-equilibrium bubbles:

$$n_x = \frac{128\pi\gamma^3}{81\sigma_c^2 k_b T}$$

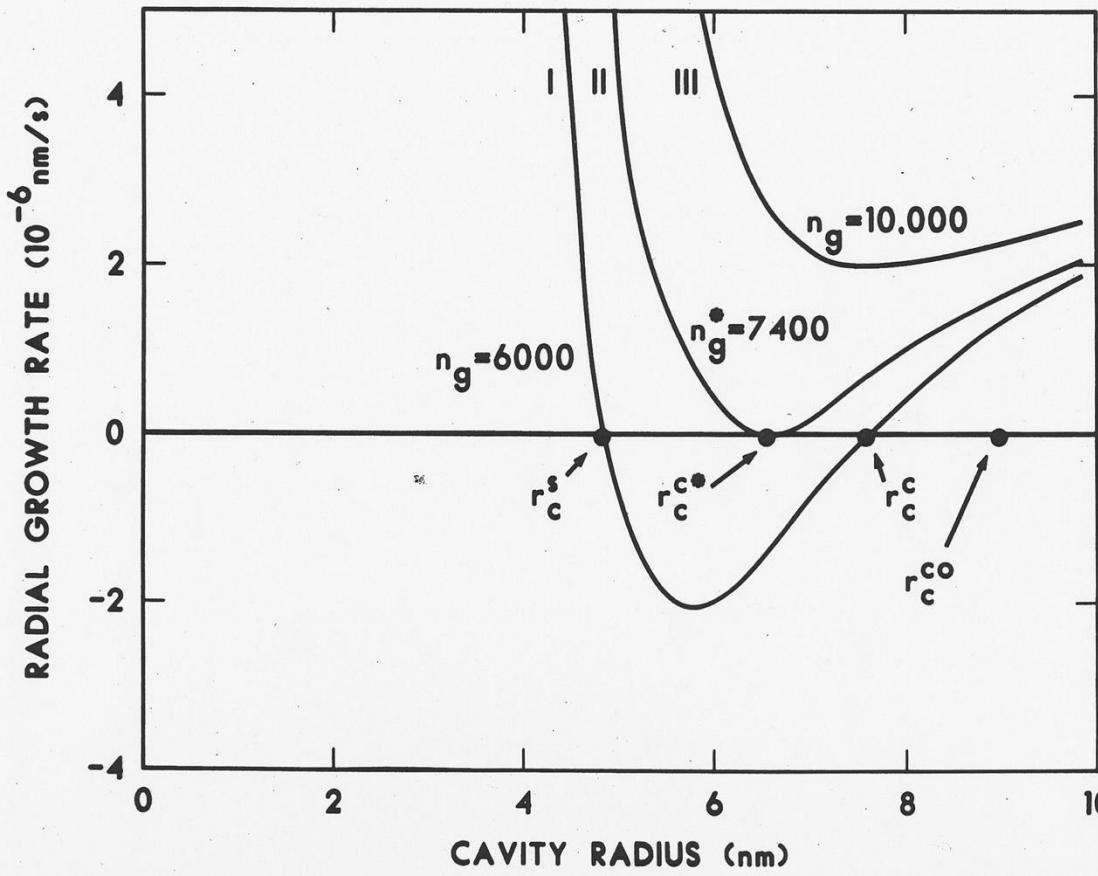


Now that we have an expression for n_x and P , we can add these into the terms for the growth rate law including thermal emission, we then get:

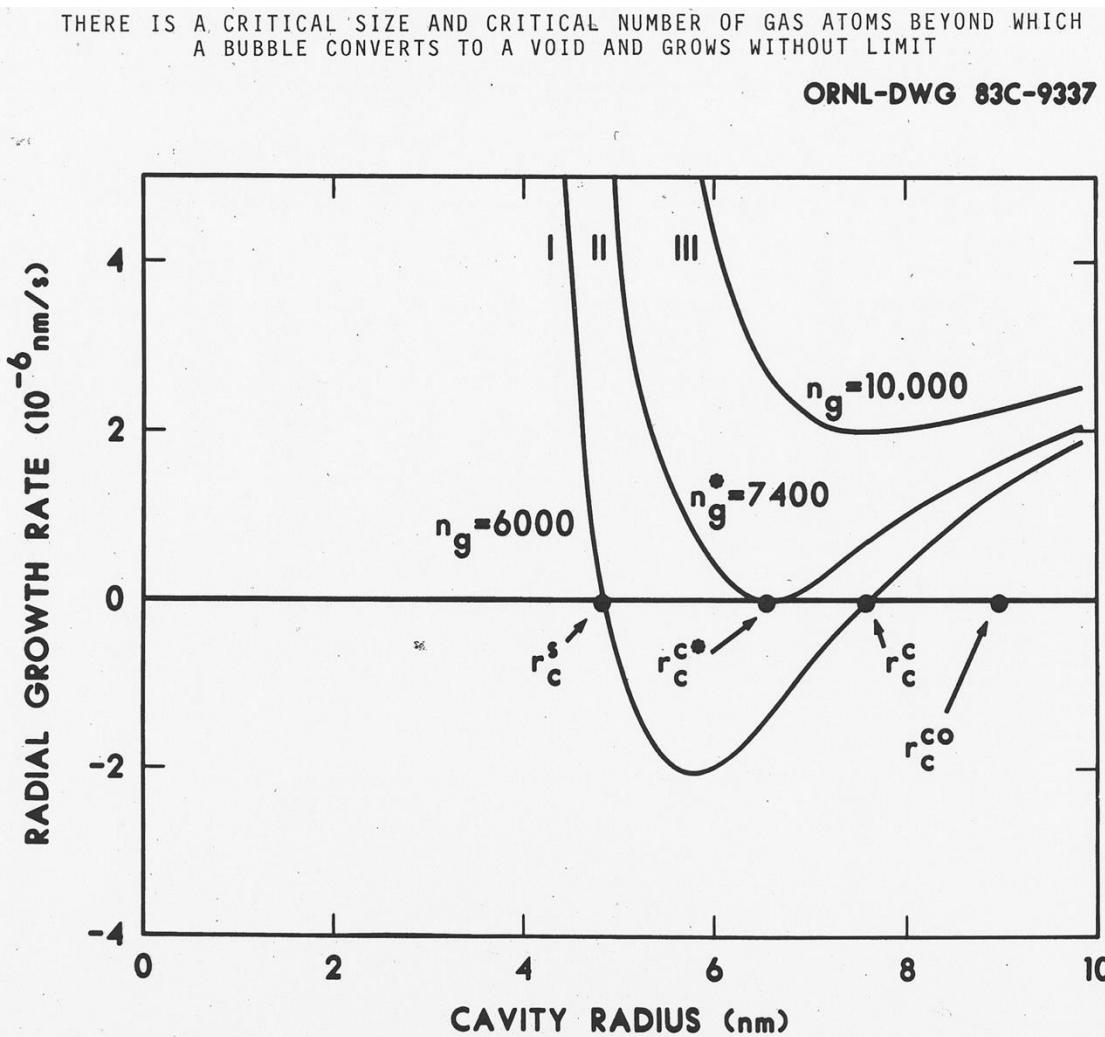
$$R\dot{R} = K_o \Omega \left(\frac{z_i - z_v}{z_v} \right) \frac{z_v \rho_d}{(4\pi R \rho_v + z_v \rho_d)^2} F(\eta) - \frac{D_v C_v^0 \Omega^2 z_v \rho_d}{kT(4\pi R N + z_v \rho_d)} \left(\frac{2\gamma}{R} - \frac{n_x kT}{4/3 \pi R^3 - n_x B} \right)$$

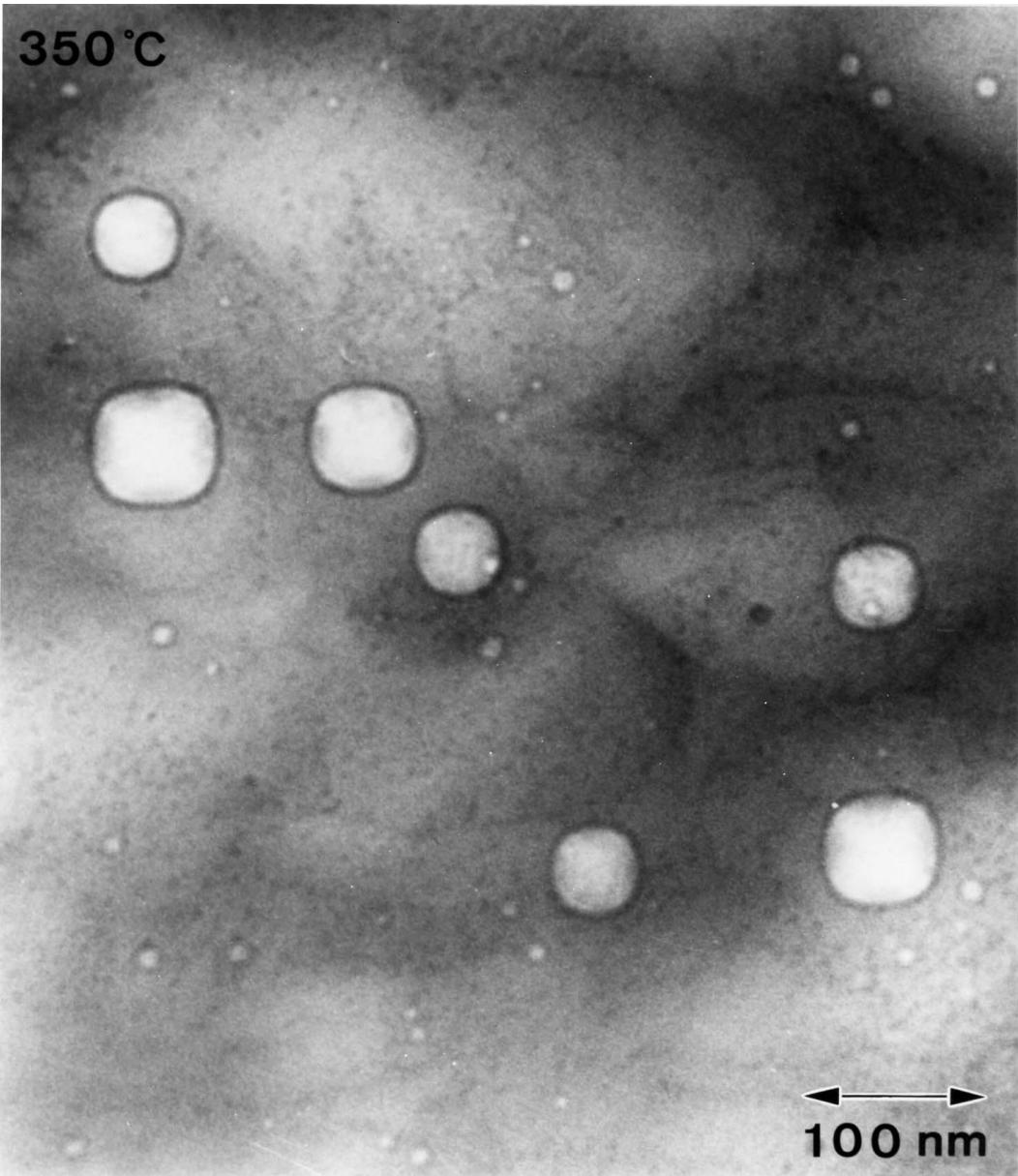
THERE IS A CRITICAL SIZE AND CRITICAL NUMBER OF GAS ATOMS BEYOND WHICH
A BUBBLE CONVERTS TO A VOID AND GROWS WITHOUT LIMIT

ORNL-DWG 83C-9337



When gas is present, the current models predicts that cavities containing less than n_g^* gas atoms remain at or below r_c^* , but those with more than n_g^* , this creates a bimodal distribution

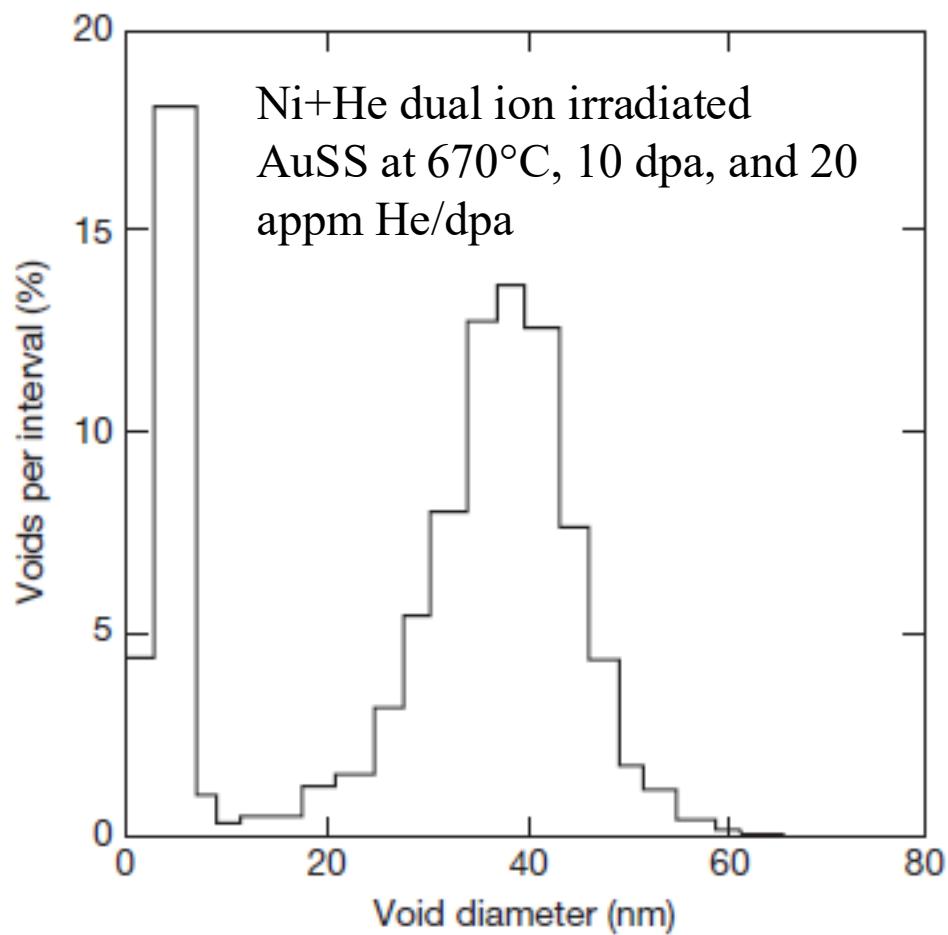




Void and He
bubble formation in
Cu-100 ppm B
following fission
neutron irradiation
to 1.2 dpa at 350°C

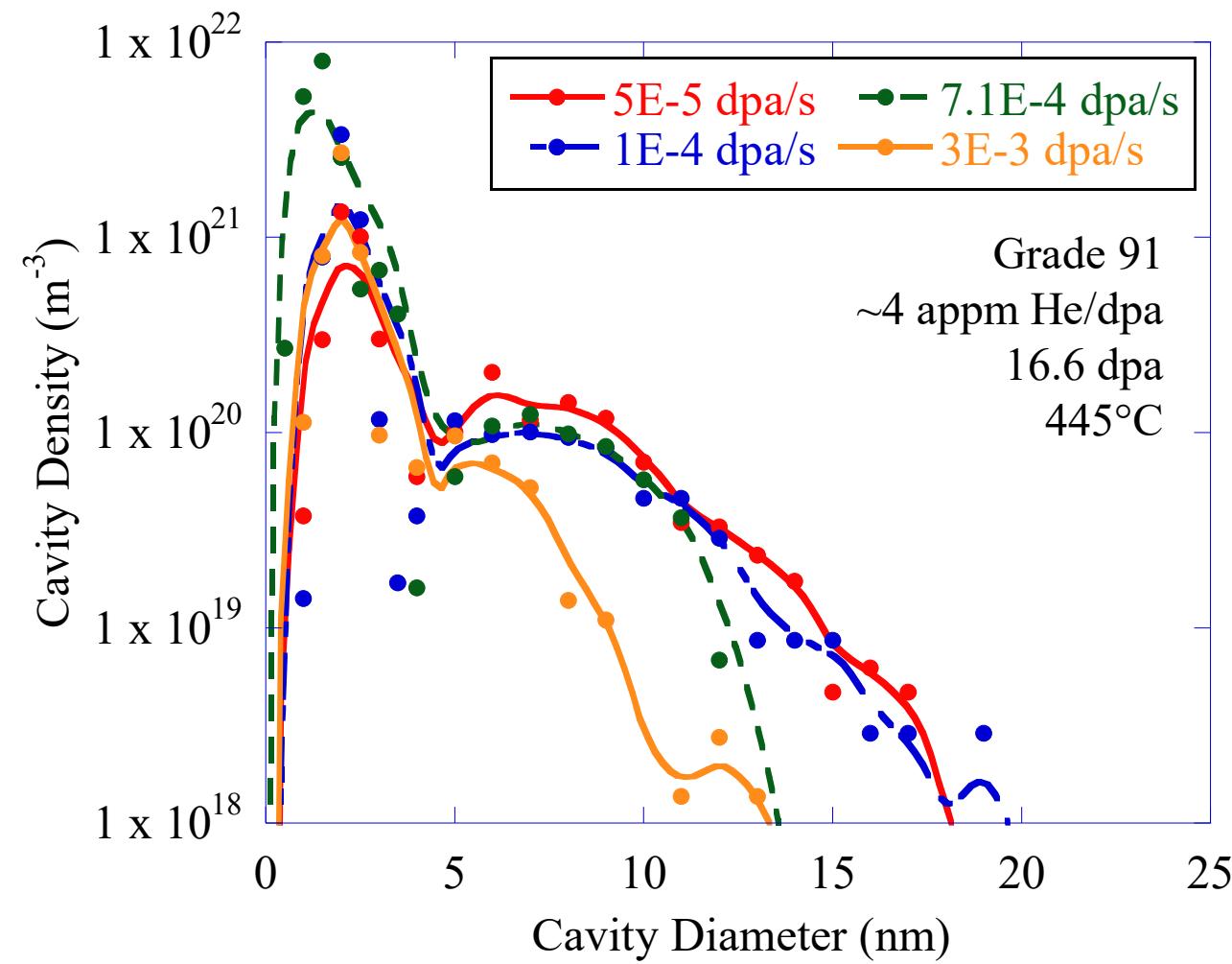
Zinkle, Farrell and Kanazawa, J. Nucl. Mater. 179-191 (1991) 994

Experimental examples



Mansur, Coghlan JNM 119 (1983)

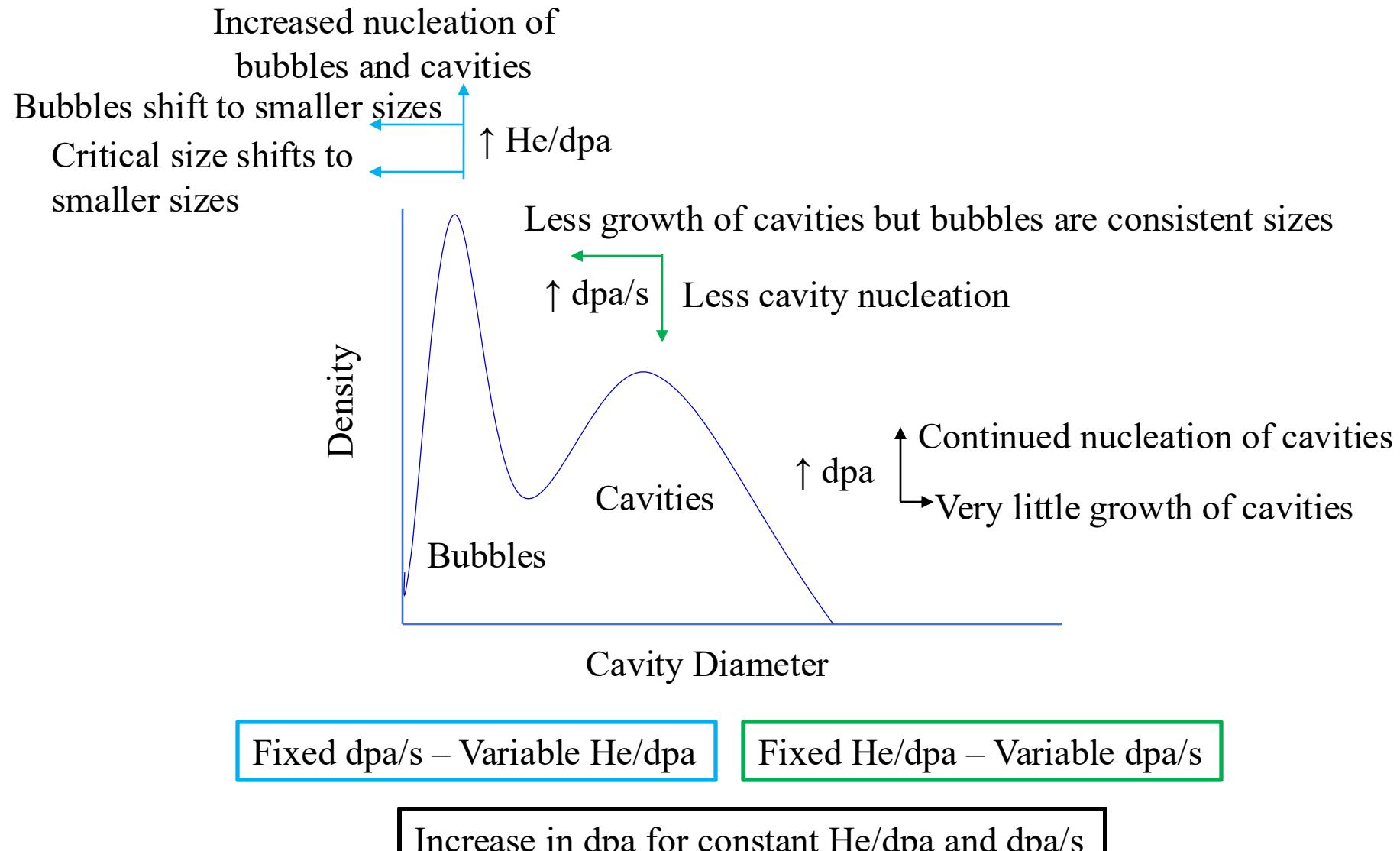
28



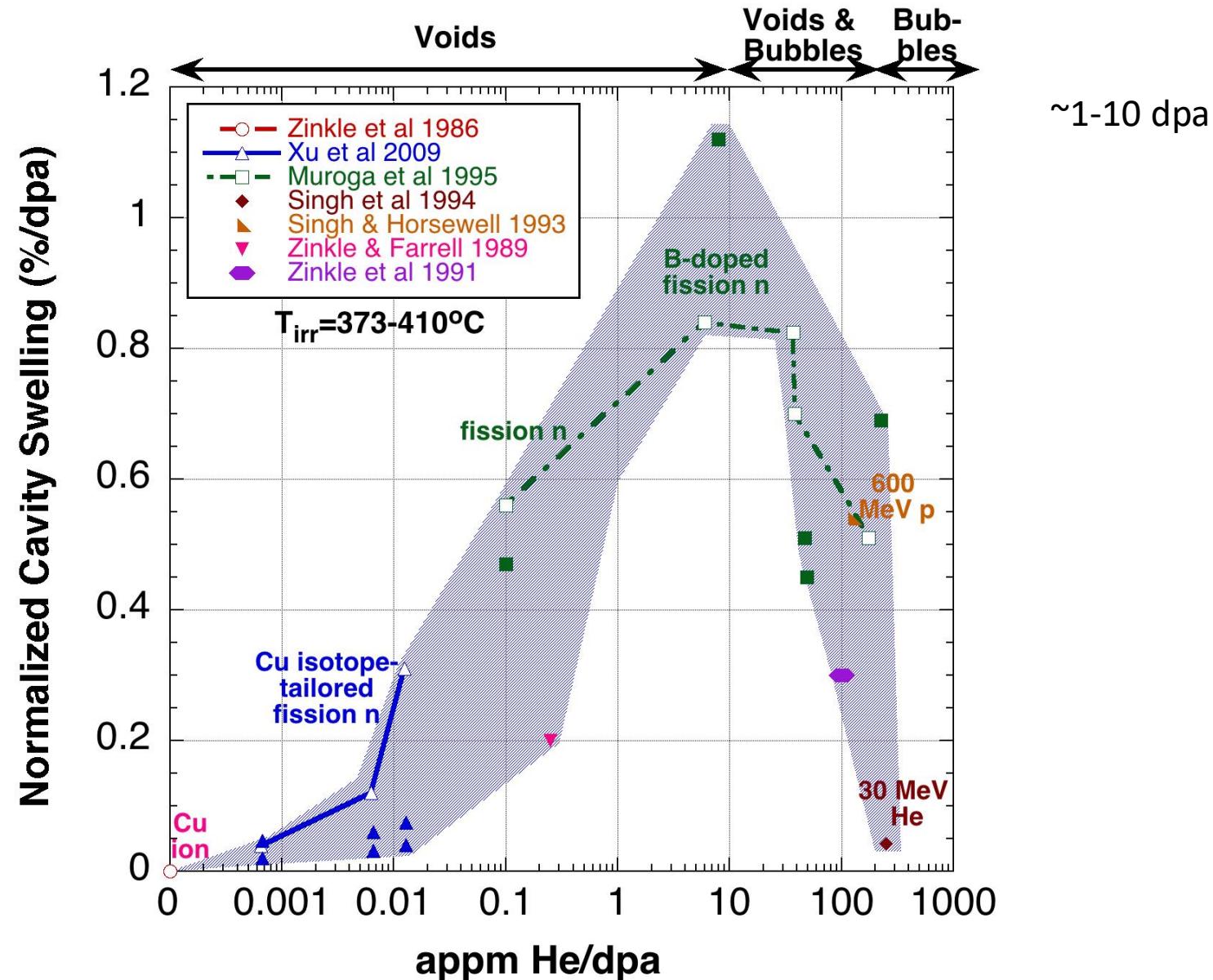
Taller (2019)



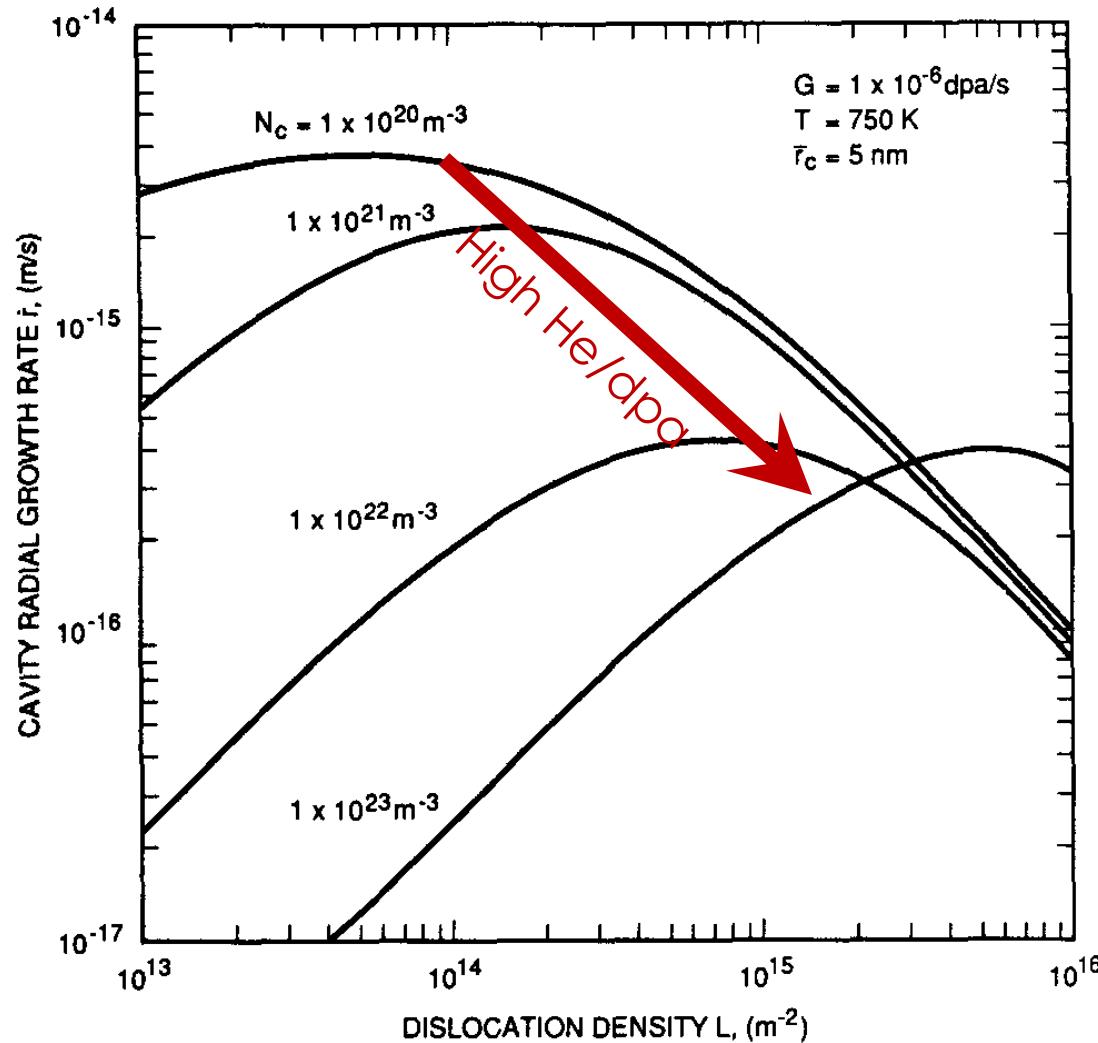
Experimental examples



Cavity swelling vs. He/dpa ratio in irradiated copper

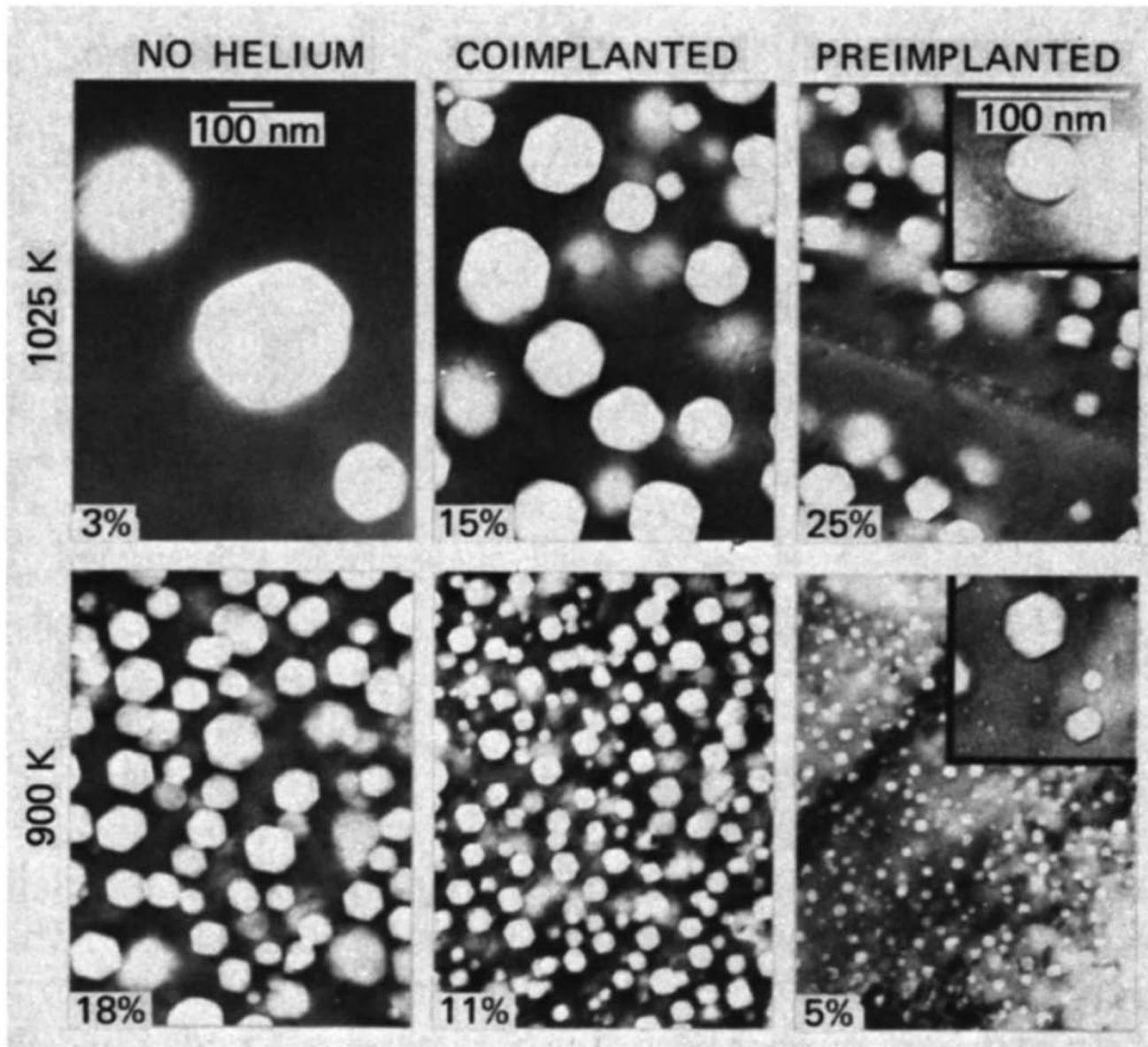


Calculated void growth rate is typically reduced for high cavity and dislocation sink strengths



Over nucleation of cavities
due to too high He/dpa
can suppress void swelling

Effect of He in ion irradiations



Implantation method of He can drastically effect swelling in ion irradiated materials

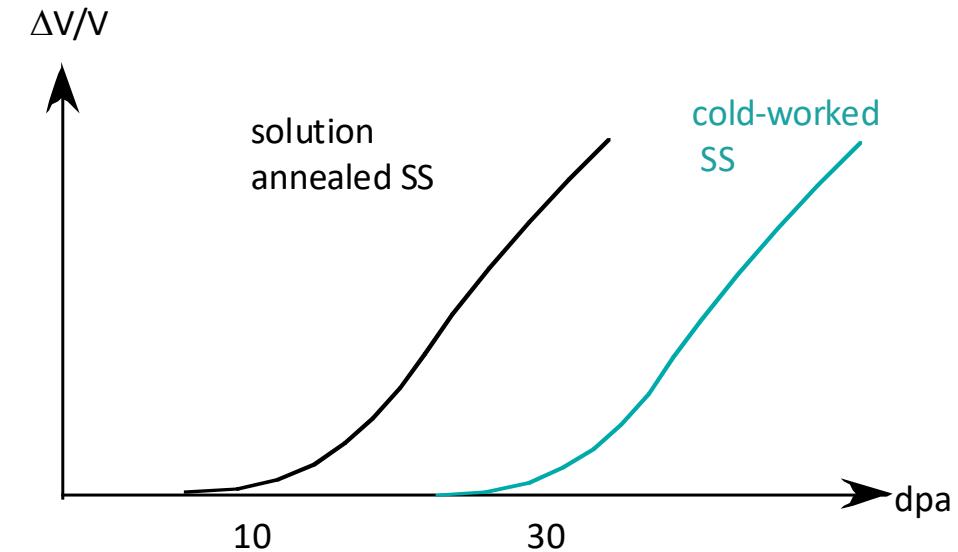
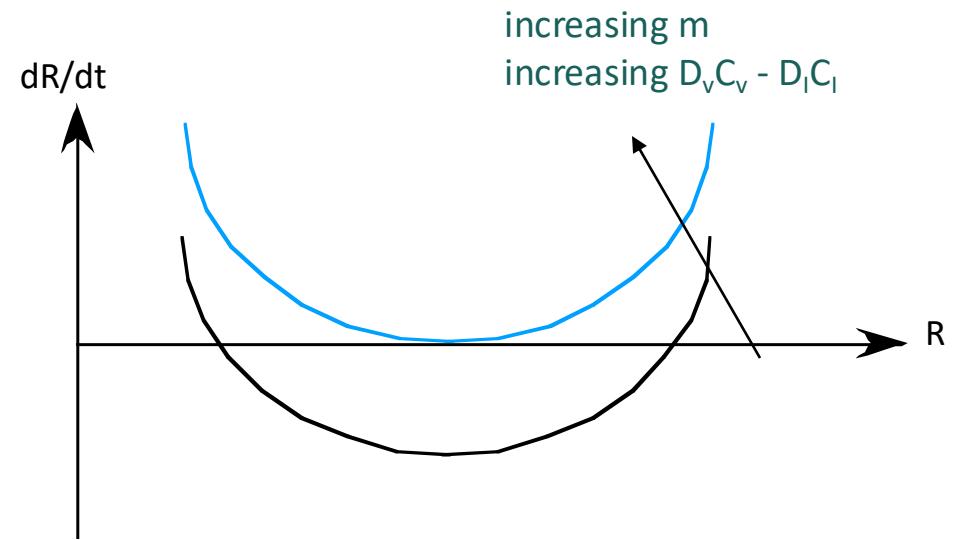
Image of
Fe-17Cr-16.7Ni-2.5Mo

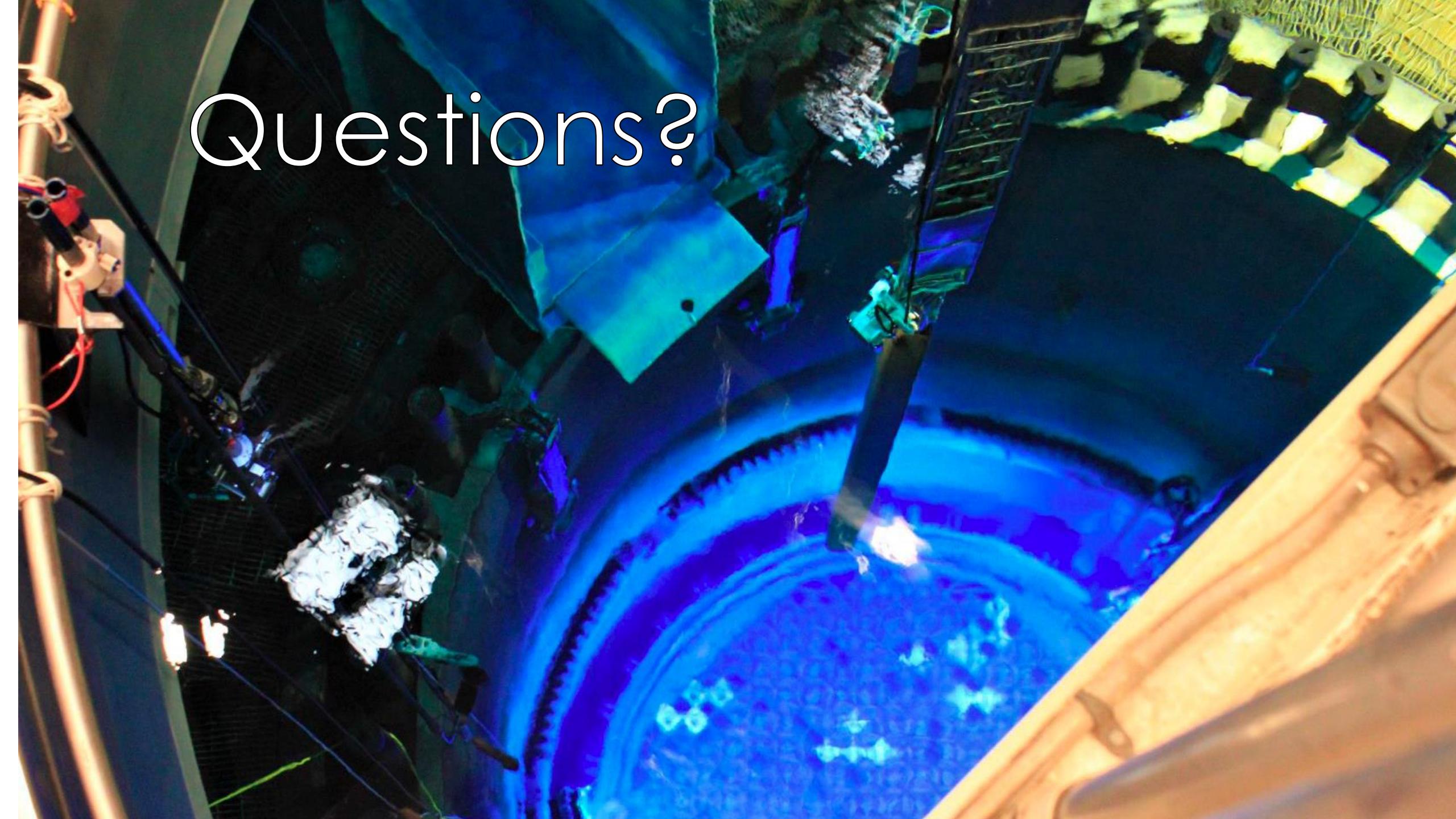
Packan & Farrell, NT-Fusion, 1983

Remedies for void swelling?

Remedies for void swelling?

- Decrease $D_v C_v - D_i C_i$ arriving at cavity;
- Eliminate He gas production
(expensive or impractical)
- Reduce C_v, C_i :
 - increase recombination
 - add precipitates or dispersoids (TiC/TiO_2) to act as recombination sink, trap He and stabilize dislocations
 - increase other sink strengths
 - add dislocations (cold-work); generally only effective for low to moderate doses
 - introduce nanoscale grain boundaries





Questions?